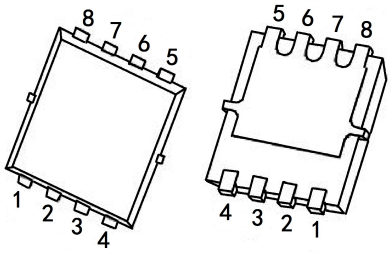
80V N-Channel Mosfet

FEATURES

- $R_{DS(ON)} \leq 4.4m\Omega$(3.7mΩ Typ.) @ V_{GS} =10V
- AEC Q101 qualified
- Green Product (RoHS compliant)
- 100% UIS TEST

PDFN5*6-8L

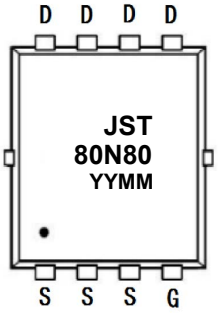


1: S	3: S	5: D	7: D
2: S	4: G	6: D	8: D

APPLICATIONS

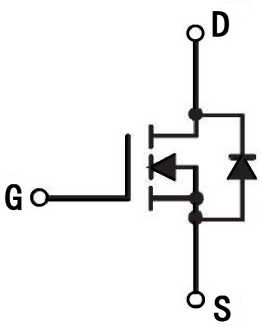
- Automotive Lighting
- High efficiency fast switching

MARKING



YYMM:Date Code(year & month)

N-CHANNEL MOSFET



MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		80	V
V_{GS}	Gate-Source Voltage		+20/-12	V
I_D	Continuous Drain Current @V_{GS}=10V	T_C = 25℃	100	A
		T_C = 100℃	70	
P_D	Power Dissipation		88	W
E_{AS}	Single pulse avalanche energy note1		484	mJ
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.7	℃/W
T_{STG}	Junction And Storage Temperature Range		-55 to +175	℃

ELECTRICAL CHARACTERISTICS TC=25 °C unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS} = 0V,I_D = 250μA	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	V_{GS} = 20V,V_{DS} = 0V	-	-	100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} =V_{GS},I_D = 250μA	2	3	4	V
$R_{DS(ON)}$	Gate Drain-Source On-State Resistance note2	V_{GS}=10V, I_D=20A	-	3.7	4.4	mΩ
Dynamic Characteristics note3						
C_{iss}	Input Capacitance	V_{DS} =30V, V_{GS} = 0V, f = 1.0MHz	-	5500	-	pF
C_{oss}	Output Capacitance		-	970	-	pF
C_{rss}	Reverse Transfer Capacitance		-	35	-	pF
Rg	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	-	1.5	-	Ω
Q_g	Total Gate Charge	V_{DS}=40V, V_{GS}=10V,I_D=10A	-	95	-	nC
Q_{gs}	Gate-Source Charge		-	23	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	32	-	nC
Switching Characteristics note3						
$t_{d(on)}$	Turn-On Delay Time	V_{DS}=40V, I_D=1A V_{GS} = 10V,R_G=6Ω,	-	22	-	ns
t_r	Turn-On Rise Time		-	16	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	40	-	ns
t_f	Turn-Off Fall Time		-	19	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_{SD}=10A,	-	0.72	1.2	V

Notes: 1. Starting TJ=25℃ VDD=25V,VGS=10V,L=0.5mH,IAS=44A

2 . Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

3. Guaranteed by design, not subject to production testing

Typical Performance Characteristics

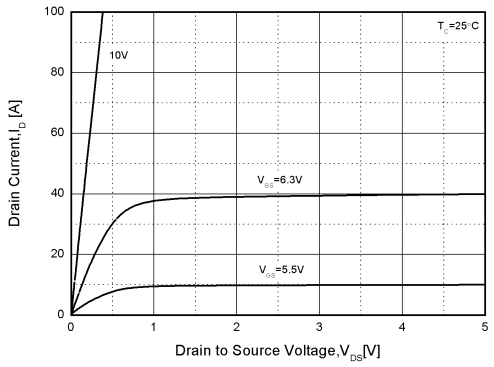


Figure1. Output Characteristics

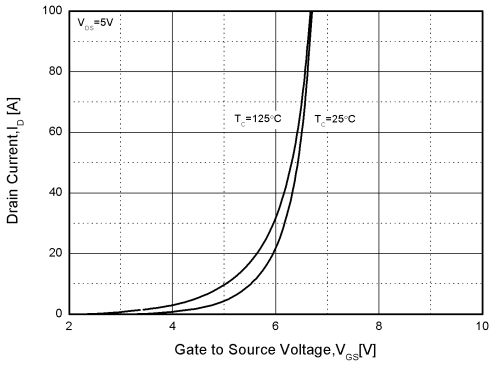


Figure2. Transfer Characteristics

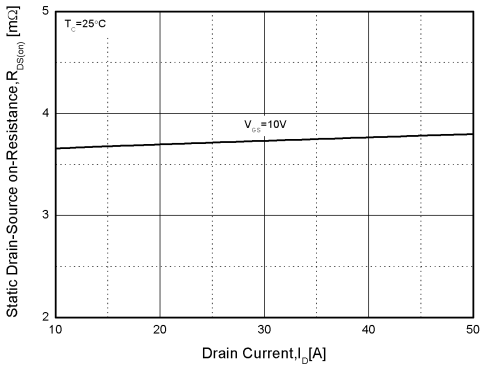


Figure3. Rdson-Drain Current

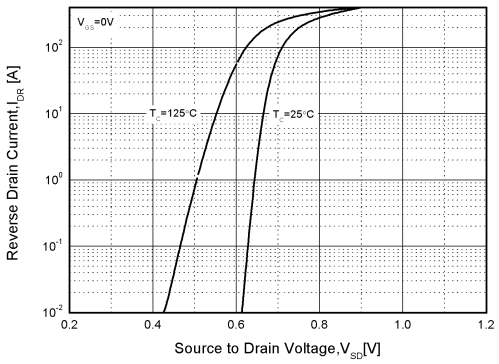


Figure4. Typical Source-Drain Diode Forward Voltage

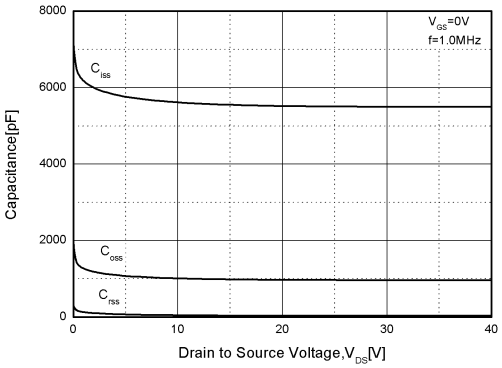


Figure5. Capacitance Characteristics

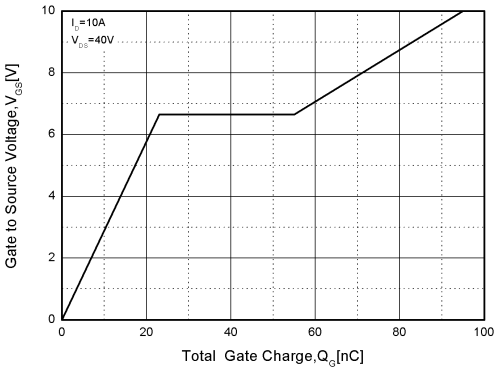


Figure6. Gate Charge

Typical Performance Characteristics (cont.)

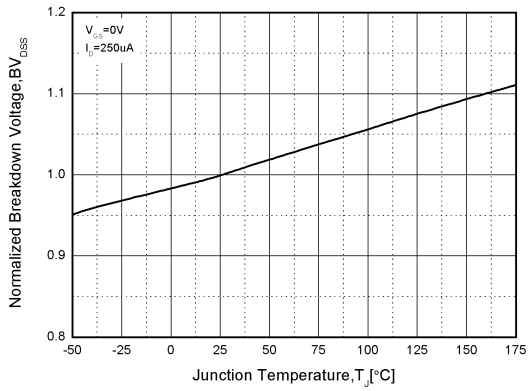


Figure7. Normalized Breakdown Voltage vs. Temperature

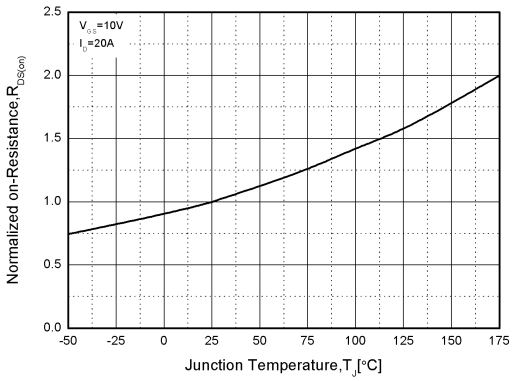


Figure8. Normalized on Resistance vs. Temperature

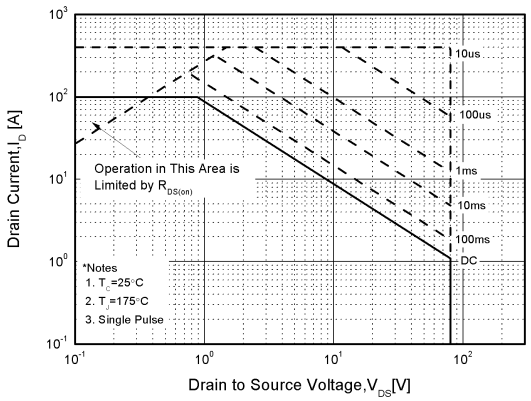


Figure9. Safe Operation Area

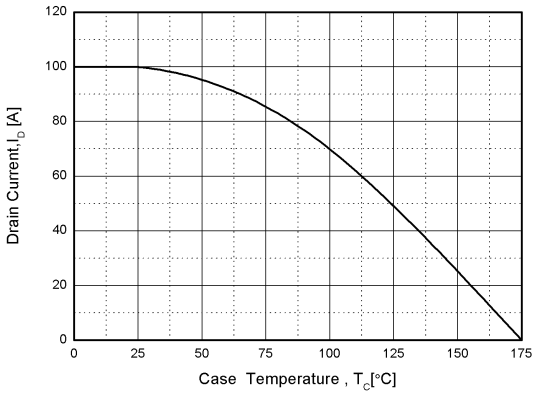


Figure10. Drain Current vs. Case Temperature

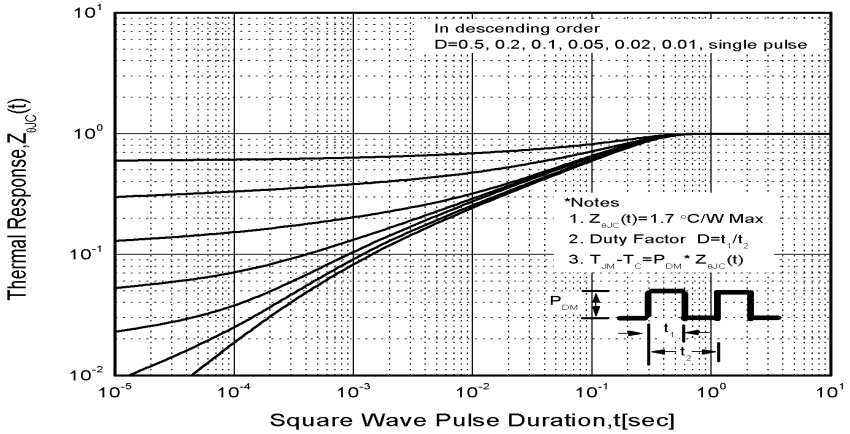
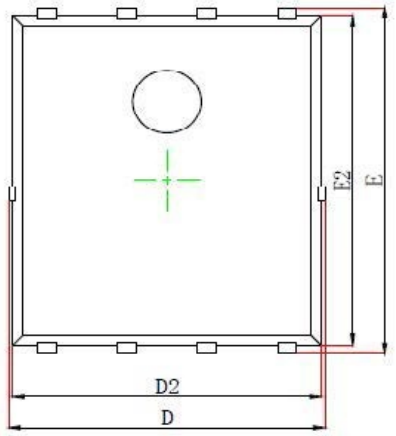
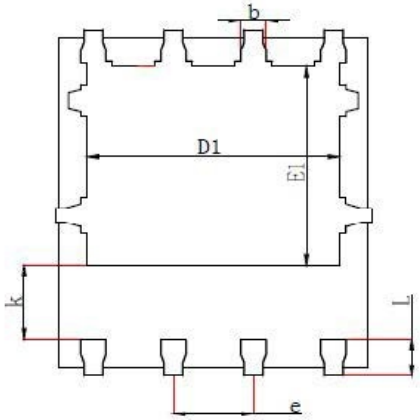


Figure11. Transient Thermal Response Curve

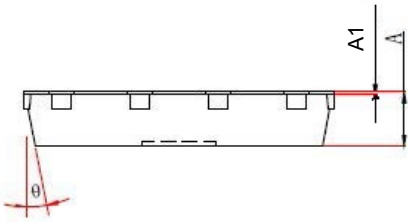
PDFN5x6-8L PACKAGE OUTLINE DRAWING



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.800	1.100	0.031	0.043
A1	0.000	0.05	0.000	0.002
D	-	5.4	-	0.212
E	-	6.200	-	0.244
D1	3.900	4.200	0.153	0.165
E1	3.350	3.650	0.132	0.144
D2	4.800	5.100	0.189	0.201
E2	5.674	5.950	0.223	0.234
k	1.100	1.500	0.043	0.059
b	0.250	0.490	0.010	0.019
e	1.170	1.370		
L	0.510	0.711	0.020	0.028
θ	6°	14°	6°	14°